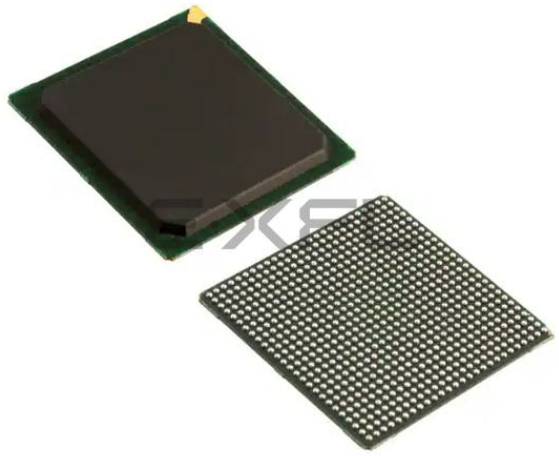


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

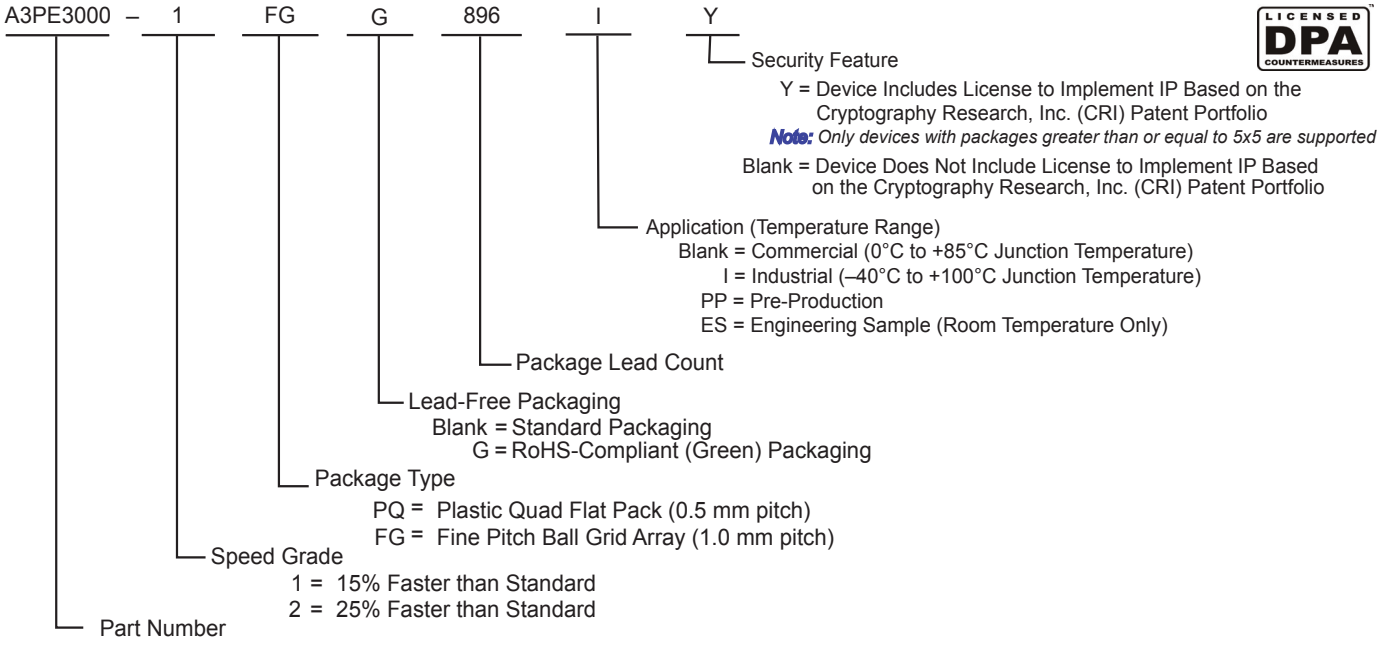
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	444
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	676-BGA
Supplier Device Package	676-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe1500-2fgg676i

ProASIC3E Ordering Information



ProASIC3E Devices

A3PE600 = 600,000 System Gates
A3PE1500 = 1,500,000 System Gates
A3PE3000 = 3,000,000 System Gates

ProASIC3E Devices with Cortex-M1

M1A3PE1500 = 1,500,000 System Gates
M1A3PE3000 = 3,000,000 System Gates

Table 2-2 • Recommended Operating Conditions [1]

Symbol	Parameter		Commercial	Industrial	Units
T_A	Ambient temperature		0 to +70	–40 to +85	°C
T_J	Junction temperature		0 to +85	–40 to +100	°C
VCC	1.5 V DC core supply voltage		1.425 to 1.575	1.425 to 1.575	V
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage	Programming Mode[2]	3.15 to 3.45	3.15 to 3.45	V
		Operation[3]	0 to 3.6	0 to 3.6	V
VCCPLL	Analog power supply (PLL)		1.425 to 1.575	1.425 to 1.575	V
VCCI and VMV [4]	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.3 V DC supply voltage		3.0 to 3.6	3.0 to 3.6	V
	3.0 V DC supply voltage[5]		2.7 to 3.6	2.7 to 3.6	V
	LVDS/B-LVDS/M-LVDS differential I/O		2.375 to 2.625	2.375 to 2.625	V
	LVPECL differential I/O		3.0 to 3.6	3.0 to 3.6	V

Notes:

1. *All parameters representing voltages are measured with respect to GND unless otherwise specified.*
2. *The programming temperature range supported is $T_{ambient}$ = 0°C to 85°C.*
3. *VPUMP can be left floating during normal operation (not programming mode).*
4. *The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-13 on page 2-16. VMV and VCCI should be at the same voltage within a given I/O bank. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.*
5. *To ensure targeted reliability standards are met across ambient and junction operating temperatures, Microsemi recommends that the user follow best design practices using Microsemi's timing and power simulation tools.*
6. *3.3 V wide range is compliant to the JESD8-B specification and supports 3.0 V VCCI operation.*

Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature [1]

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T_{STG} (°C) [2]	Maximum Operating Junction Temperature T_J (°C) [2]
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

Notes:

1. *This is a stress rating only; functional operation at any condition other than those indicated is not implied.*
2. *These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 for device operating conditions and absolute limits.*

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLXL exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see Figure 2-1 on page 2-4 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V ± 0.25 V), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *ProASIC3E FPGA Fabric User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

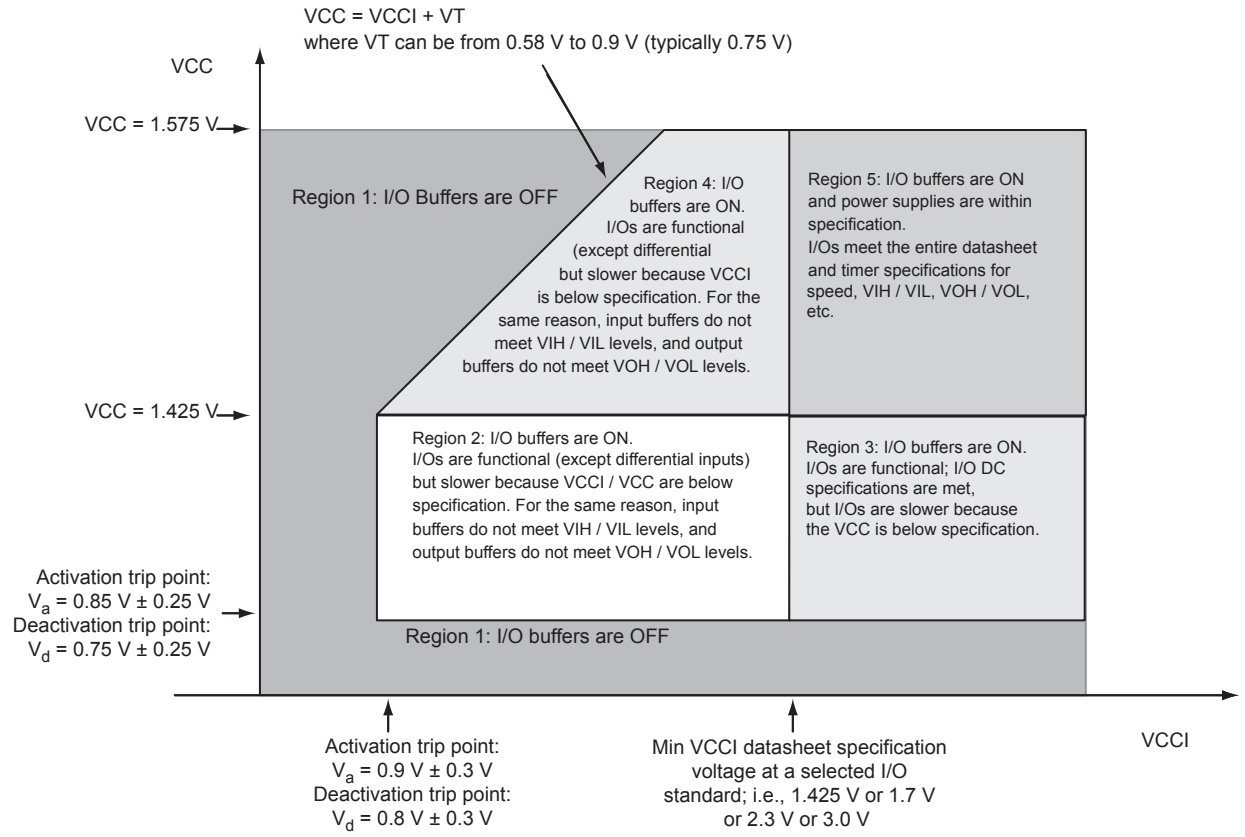


Figure 2-1 • **I/O State as a Function of VCCI and VCC Voltage Levels**

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in the Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-11 on page 2-11.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-12 on page 2-11.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-12 on page 2-11. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

$P_{STAT} = PDC1 + N_{INPUTS} * PDC2 + N_{OUTPUTS} * PDC3$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S\text{-}CELL} * PAC4) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution—$P_{S\text{-}CELL}$

$P_{S\text{-}CELL} = N_{S\text{-}CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-11 on page 2-11.

F_{CLK} is the global clock signal frequency.

Table 2-14 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions

	Commercial[1]		Industrial[2]	
	IIL[3]	IIH[4]	IIL[3]	IIH[4]
DC I/O Standards	µA	µA	µA	µA
3.3 V LVTTL / 3.3 V LVCMOS	10	10	15	15
3.3 V LVCMOS Wide Range	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
3.3 V PCI	10	10	15	15
3.3 V PCI-X	10	10	15	15
3.3 V GTL	10	10	15	15
2.5 V GTL	10	10	15	15
3.3 V GTL+	10	10	15	15
2.5 V GTL+	10	10	15	15
HSTL (I)	10	10	15	15
HSTL (II)	10	10	15	15
SSTL2 (I)	10	10	15	15
SSTL2 (II)	10	10	15	15
SSTL3 (I)	10	10	15	15
SSTL3 (II)	10	10	15	15

Notes:

1. *Commercial range (0°C < T_A < 70°C)*
2. *Industrial range (–40°C < T_A < 85°C)*
3. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
4. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*

Table 2-36 • 2.5 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	12.00	0.04	1.51	1.66	0.43	12.23	11.61	2.72	2.20	14.46	13.85	ns
	–1	0.56	10.21	0.04	1.29	1.41	0.36	10.40	9.88	2.31	1.87	12.30	11.78	ns
	–2	0.49	8.96	0.03	1.13	1.24	0.32	9.13	8.67	2.03	1.64	10.80	10.34	ns
8 mA	Std.	0.66	8.73	0.04	1.51	1.66	0.43	8.89	8.01	3.10	2.93	11.13	10.25	ns
	–1	0.56	7.43	0.04	1.29	1.41	0.36	7.57	6.82	2.64	2.49	9.47	8.72	ns
	–2	0.49	6.52	0.03	1.13	1.24	0.32	6.64	5.98	2.32	2.19	8.31	7.65	ns
12 mA	Std.	0.66	6.77	0.04	1.51	1.66	0.43	6.90	6.11	3.37	3.39	9.14	8.34	ns
	–1	0.56	5.76	0.04	1.29	1.41	0.36	5.87	5.20	2.86	2.89	7.77	7.10	ns
	–2	0.49	5.06	0.03	1.13	1.24	0.32	5.15	4.56	2.51	2.53	6.82	6.23	ns
16 mA	Std.	0.66	6.31	0.04	1.51	1.66	0.43	6.42	5.73	3.42	3.52	8.66	7.96	ns
	–1	0.56	5.37	0.04	1.29	1.41	0.36	5.46	4.87	2.91	3.00	7.37	6.77	ns
	–2	0.49	4.71	0.03	1.13	1.24	0.32	4.80	4.28	2.56	2.63	6.47	5.95	ns
24 mA	Std.	0.66	5.93	0.04	1.51	1.66	0.43	6.04	5.70	3.49	4.00	8.28	7.94	ns
	–1	0.56	5.05	0.04	1.29	1.41	0.36	5.14	4.85	2.97	3.40	7.04	6.75	ns
	–2	0.49	4.43	0.03	1.13	1.24	0.32	4.51	4.26	2.61	2.99	6.18	5.93	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Voltage-Referenced I/O Characteristics

3.3 V GTL

Gunning Transceiver Logic is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 3.3 V.

Table 2-48 • Minimum and Maximum DC Input and Output Levels

3.3 V GTL	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
20 mA[3]	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20	181	268	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Output drive strength is below JEDEC specification.*

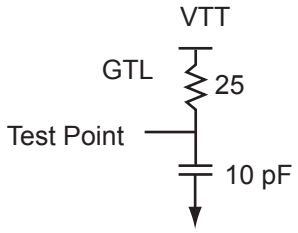


Figure 2-12 • AC Loading

Table 2-49 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.05	VREF + 0.05	0.8	0.8	1.2	10

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-50 • 3.3 V GTL
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V VREF = 0.8 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.60	2.08	0.04	2.93	0.43	2.04	2.08			4.27	4.31	ns
–1	0.51	1.77	0.04	2.50	0.36	1.73	1.77			3.63	3.67	ns
–2	0.45	1.55	0.03	2.19	0.32	1.52	1.55			3.19	3.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

2.5 V GTL

Gunning Transceiver Logic is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 2.5 V.

Table 2-51 • Minimum and Maximum DC Input and Output Levels

2.5 GTL	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min., V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
20 mA[3]	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20	124	169	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Output drive strength is below JEDEC specification.*

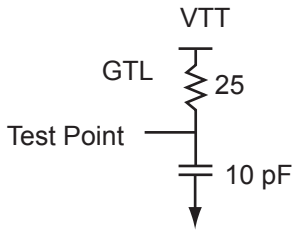


Figure 2-13 • AC Loading

Table 2-52 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.05	VREF + 0.05	0.8	0.8	1.2	10

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-53 • 2.5 V GTL
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V VREF = 0.8 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.60	2.13	0.04	2.46	0.43	2.16	2.13			4.40	4.36	ns
–1	0.51	1.81	0.04	2.09	0.36	1.84	1.81			3.74	3.71	ns
–2	0.45	1.59	0.03	1.83	0.32	1.61	1.59			3.28	3.26	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

SSTL2 Class I

Stub-Speed Terminated Logic for 2.5 V memory bus standard (JESD8-9). ProASIC3E devices support Class I. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-66 • Minimum and Maximum DC Input and Output Levels

SSTL2 Class I	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
15 mA	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.54	VCCI – 0.62	15	15	87	83	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

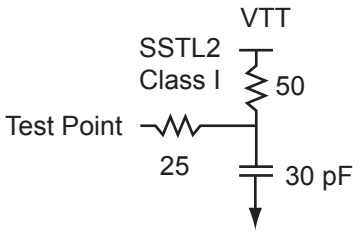


Figure 2-18 • AC Loading

Table 2-67 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.2	VREF + 0.2	1.25	1.25	1.25	30

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-68 • SSTL 2 Class I
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V, VREF = 1.25 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	2.13	0.04	1.33	0.43	2.17	1.85			4.40	4.08	ns
–1	0.56	1.81	0.04	1.14	0.36	1.84	1.57			3.74	3.47	ns
–2	0.49	1.59	0.03	1.00	0.32	1.62	1.38			3.29	3.05	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Differential I/O Characteristics

Physical Implementation

Configuration of the I/O modules as a differential pair is handled by the Designer software when the user instantiates a differential I/O macro in the design.

Differential I/Os can also be used in conjunction with the embedded Input Register (InReg), Output Register (OutReg), Enable Register (EnReg), and DDR. However, there is no support for bidirectional I/Os or tristates with the LVPECL standards.

LVDS

Low-Voltage Differential Signaling (ANSI/TIA/EIA-644) is a high-speed, differential I/O standard. It requires that one data bit be carried through two signal lines, so two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-22. The building blocks of the LVDS transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVPECL implementation because the output standard specifications are different.

Along with LVDS I/O, ProASIC3E also supports Bus LVDS structure and Multipoint LVDS (M-LVDS) configuration (up to 40 nodes).

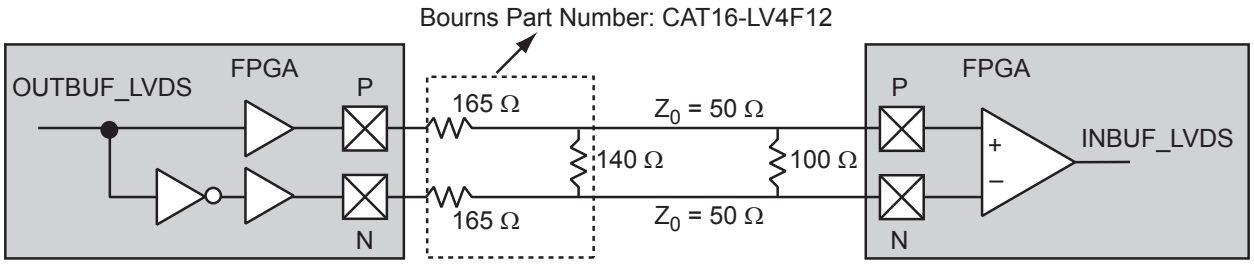


Figure 2-22 • **LVDS Circuit Diagram and Board-Level Implementation**

***Table 2-84* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

*Note: *See Figure 2-25 on page 2-53 for more information.*

Output Enable Register

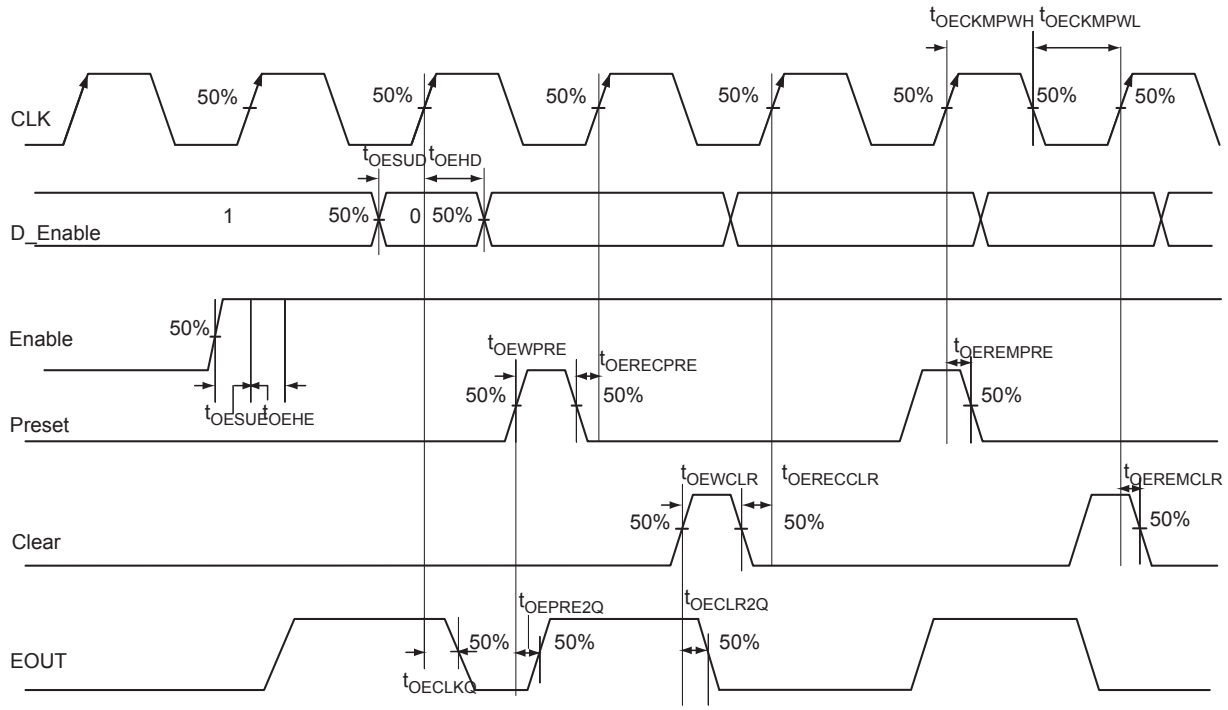


Figure 2-29 • **Output Enable Register Timing Diagram**

Timing Characteristics

Table 2-88 • **Output Enable Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.59	0.67	0.79	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.31	0.36	0.42	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.44	0.50	0.58	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.36	0.41	0.48	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Timing Characteristics

Table 2-93 • Combinatorial Cell Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Combinatorial Cell	Equation	Parameter	–2	–1	Std.	Units
INV	Y = !A	t_{PD}	0.40	0.46	0.54	ns
AND2	Y = A · B	t_{PD}	0.47	0.54	0.63	ns
NAND2	Y = !(A · B)	t_{PD}	0.47	0.54	0.63	ns
OR2	Y = A + B	t_{PD}	0.49	0.55	0.65	ns
NOR2	Y = !(A + B)	t_{PD}	0.49	0.55	0.65	ns
XOR2	Y = A ⊕ B	t_{PD}	0.74	0.84	0.99	ns
MAJ3	Y = MAJ(A , B, C)	t_{PD}	0.70	0.79	0.93	ns
XOR3	Y = A ⊕ B ⊕ C	t_{PD}	0.87	1.00	1.17	ns
MUX2	Y = A !S + B S	t_{PD}	0.51	0.58	0.68	ns
AND3	Y = A · B · C	t_{PD}	0.56	0.64	0.75	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

VersaTile Specifications as a Sequential Module

The ProASIC3E library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library. For more details, refer to the *Fusion, IGLOO/e, and ProASIC3/E Macro Library Guide*.

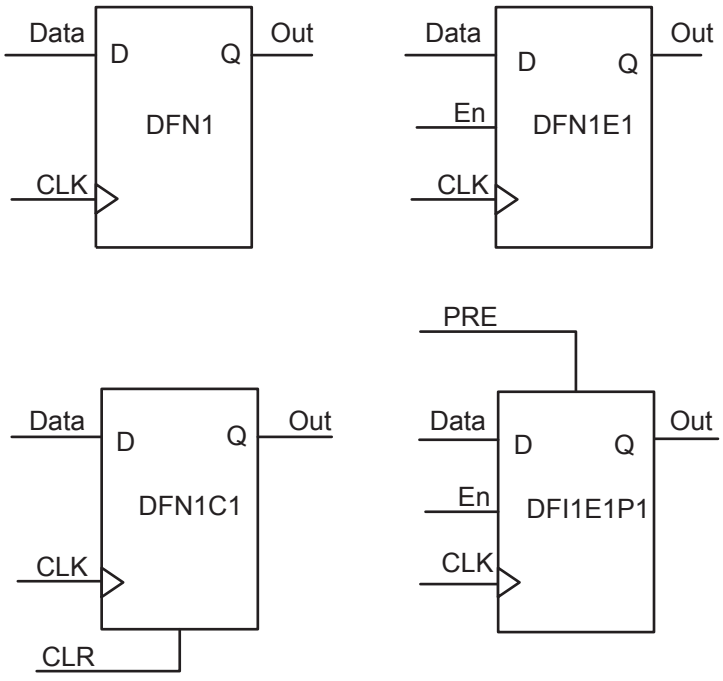


Figure 2-36 • Sample of Sequential Cells

Clock Conditioning Circuits

CCC Electrical Specifications

Timing Characteristics

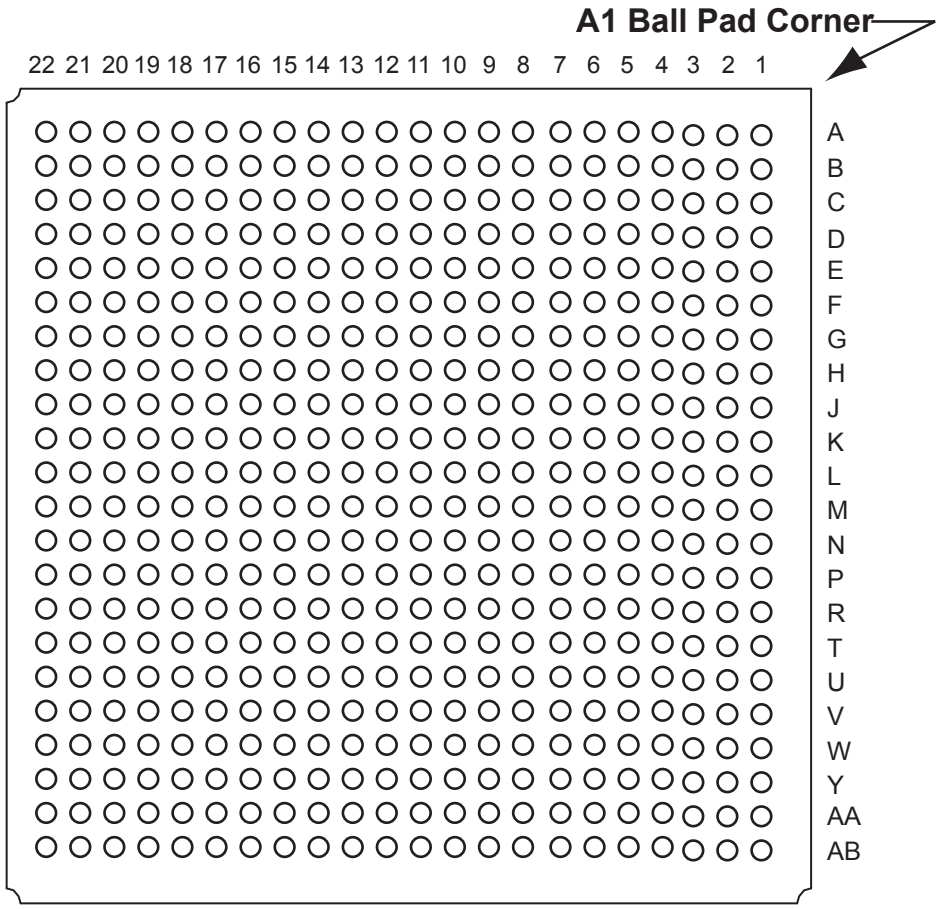
Table 2-98 • ProASIC3E CCC/PLL Specification

Parameter		Minimum	Typical	Maximum	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}		1.5		350	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}		0.75		350	MHz
Delay Increments in Programmable Delay Blocks [1, 2]			160[3]		ps
Serial Clock (SCLK) for Dynamic PLL[4]				125	MHz
Number of Programmable Values in Each Programmable Delay Block				32	
Input Period Jitter				1.5	ns
CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT}		Max Peak-to-Peak Period Jitter			
		1 Global Network Used		3 Global Networks Used	
0.75 MHz to 24 MHz		0.50%		0.70%	
24 MHz to 100 MHz		1.00%		1.20%	
100 MHz to 250 MHz		1.75%		2.00%	
250 MHz to 350 MHz		2.50%		5.60%	
Acquisition Time	LockControl = 0			300	µs
	LockControl = 1			6.0	ms
Tracking Jitter[5]	LockControl = 0			1.6	ns
	LockControl = 1			0.8	ns
Output Duty Cycle		48.5		51.5	%
Delay Range in Block: Programmable Delay 1 [1, 2]		0.6		5.56	ns
Delay Range in Block: Programmable Delay 2 [1,2]		0.025		5.56	ns
Delay Range in Block: Fixed Delay[1,4]			2.2		ns

Notes:

1. *This delay is a function of voltage and temperature. See Table 2-6 on page 2-5 for deratings*
2. *T_J = 25°C, VCC = 1.5 V.*
3. *When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help for more information.*
4. *Maximum value obtained for a –2 speed-grade device in worst-case commercial conditions. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*
5. *Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to the PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by the period jitter parameter.*

FG484



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

FG484	
Pin Number	A3PE600 Function
A1	GND
A2	GND
A3	VCCIB0
A4	IO06NDB0V1
A5	IO06PDB0V1
A6	IO08NDB0V1
A7	IO08PDB0V1
A8	IO11PDB0V1
A9	IO17PDB0V2
A10	IO18NDB0V2
A11	IO18PDB0V2
A12	IO22PDB1V0
A13	IO26PDB1V0
A14	IO29NDB1V1
A15	IO29PDB1V1
A16	IO31NDB1V1
A17	IO31PDB1V1
A18	IO32NDB1V1
A19	NC
A20	VCCIB1
A21	GND
A22	GND
AA1	GND
AA2	VCCIB6
AA3	NC
AA4	IO98PDB5V2
AA5	IO96NDB5V2
AA6	IO96PDB5V2
AA7	IO86NDB5V0
AA8	IO86PDB5V0
AA9	IO85PDB5V0
AA10	IO85NDB5V0
AA11	IO78PPB4V1
AA12	IO79NDB4V1
AA13	IO79PDB4V1
AA14	NC

FG484	
Pin Number	A3PE600 Function
AA15	NC
AA16	IO71NDB4V0
AA17	IO71PDB4V0
AA18	NC
AA19	NC
AA20	NC
AA21	VCCIB3
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB5
AB4	IO97NDB5V2
AB5	IO97PDB5V2
AB6	IO93NDB5V1
AB7	IO93PDB5V1
AB8	IO87NDB5V0
AB9	IO87PDB5V0
AB10	NC
AB11	NC
AB12	IO75NDB4V1
AB13	IO75PDB4V1
AB14	IO72NDB4V0
AB15	IO72PDB4V0
AB16	IO73NDB4V0
AB17	IO73PDB4V0
AB18	NC
AB19	NC
AB20	VCCIB4
AB21	GND
AB22	GND
B1	GND
B2	VCCIB7
B3	NC
B4	IO03NDB0V0
B5	IO03PDB0V0
B6	IO07NDB0V1

FG484	
Pin Number	A3PE600 Function
B7	IO07PDB0V1
B8	IO11NDB0V1
B9	IO17NDB0V2
B10	IO14PDB0V2
B11	IO19PDB0V2
B12	IO22NDB1V0
B13	IO26NDB1V0
B14	NC
B15	NC
B16	IO30NDB1V1
B17	IO30PDB1V1
B18	IO32PDB1V1
B19	NC
B20	NC
B21	VCCIB2
B22	GND
C1	VCCIB7
C2	NC
C3	NC
C4	NC
C5	GND
C6	IO04NDB0V0
C7	IO04PDB0V0
C8	VCC
C9	VCC
C10	IO14NDB0V2
C11	IO19NDB0V2
C12	NC
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC

FG484	
Pin Number	A3PE600 Function
H19	IO41PDB2V0
H20	VCC
H21	NC
H22	NC
J1	IO123NDB7V0
J2	IO123PDB7V0
J3	NC
J4	IO124PDB7V0
J5	IO125PDB7V0
J6	IO126PDB7V0
J7	IO130NDB7V1
J8	VCCIB7
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB2
J16	IO38NDB2V0
J17	IO40NDB2V0
J18	IO40PDB2V0
J19	IO45PPB2V1
J20	NC
J21	IO48PDB2V1
J22	IO46PDB2V1
K1	IO121NDB7V0
K2	IO121PDB7V0
K3	NC
K4	IO124NDB7V0
K5	IO125NDB7V0
K6	IO126NDB7V0
K7	GFC1/IO120PPB7V0
K8	VCCIB7
K9	VCC
K10	GND

FG484	
Pin Number	A3PE600 Function
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB2
K16	GCC1/IO50PPB2V1
K17	IO44NDB2V1
K18	IO44PDB2V1
K19	IO49NPB2V1
K20	IO45NPB2V1
K21	IO48NDB2V1
K22	IO46NDB2V1
L1	NC
L2	IO122PDB7V0
L3	IO122NDB7V0
L4	GFB0/IO119NPB7V0
L5	GFA0/IO118NDB6V1
L6	GFB1/IO119PPB7V0
L7	VCOMPLF
L8	GFC0/IO120NPB7V0
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	VCC
L15	GCC0/IO50NPB2V1
L16	GCB1/IO51PPB2V1
L17	GCA0/IO52NPB3V0
L18	VCOMPLC
L19	GCB0/IO51NPB2V1
L20	IO49PPB2V1
L21	IO47NDB2V1
L22	IO47PDB2V1
M1	NC
M2	IO114NPB6V1

FG484	
Pin Number	A3PE600 Function
M3	IO117NDB6V1
M4	GFA2/IO117PDB6V1
M5	GFA1/IO118PDB6V1
M6	VCCPLF
M7	IO116NDB6V1
M8	GFB2/IO116PDB6V1
M9	VCC
M10	GND
M11	GND
M12	GND
M13	GND
M14	VCC
M15	GCB2/IO54PPB3V0
M16	GCA1/IO52PPB3V0
M17	GCC2/IO55PPB3V0
M18	VCCPLC
M19	GCA2/IO53PDB3V0
M20	IO53NDB3V0
M21	IO56PDB3V0
M22	NC
N1	IO114PPB6V1
N2	IO111NDB6V1
N3	NC
N4	GFC2/IO115PPB6V1
N5	IO113PPB6V1
N6	IO112PDB6V1
N7	IO112NDB6V1
N8	VCCIB6
N9	VCC
N10	GND
N11	GND
N12	GND
N13	GND
N14	VCC
N15	VCCIB3
N16	IO54NPB3V0

FG896	
Pin Number	A3PE3000 Function
AG9	IO225NPB5V3
AG10	IO223NPB5V3
AG11	IO221PDB5V3
AG12	IO221NDB5V3
AG13	IO205NPB5V1
AG14	IO199NDB5V0
AG15	IO199PDB5V0
AG16	IO187NDB4V4
AG17	IO187PDB4V4
AG18	IO181NDB4V3
AG19	IO171PPB4V2
AG20	IO165NPB4V1
AG21	IO161NPB4V0
AG22	IO159NDB4V0
AG23	IO159PDB4V0
AG24	IO158PPB4V0
AG25	GDB2/IO155PDB4V0
AG26	GDA2/IO154PPB4V0
AG27	GND
AG28	VJTAG
AG29	VCC
AG30	IO149NDB3V4
AH1	GND
AH2	IO233NPB5V4
AH3	VCC
AH4	GEB2/IO232PPB5V4
AH5	VCCIB5
AH6	IO219NDB5V3
AH7	IO219PDB5V3
AH8	IO227NDB5V4
AH9	IO227PDB5V4
AH10	IO225PPB5V3
AH11	IO223PPB5V3
AH12	IO211NDB5V2
AH13	IO211PDB5V2
AH14	IO205PPB5V1

FG896	
Pin Number	A3PE3000 Function
AH15	IO195NDB5V0
AH16	IO185NDB4V3
AH17	IO185PDB4V3
AH18	IO181PDB4V3
AH19	IO177NDB4V2
AH20	IO171NPB4V2
AH21	IO165PPB4V1
AH22	IO161PPB4V0
AH23	IO157NDB4V0
AH24	IO157PDB4V0
AH25	IO155NDB4V0
AH26	VCCIB4
AH27	TDI
AH28	VCC
AH29	VPUMP
AH30	GND
AJ1	GND
AJ2	GND
AJ3	GEA2/IO233PPB5V4
AJ4	VCC
AJ5	IO217NPB5V2
AJ6	VCC
AJ7	IO215NPB5V2
AJ8	IO213NDB5V2
AJ9	IO213PDB5V2
AJ10	IO209NDB5V1
AJ11	IO209PDB5V1
AJ12	IO203NDB5V1
AJ13	IO203PDB5V1
AJ14	IO197NDB5V0
AJ15	IO195PDB5V0
AJ16	IO183NDB4V3
AJ17	IO183PDB4V3
AJ18	IO179NPB4V3
AJ19	IO177PDB4V2
AJ20	IO173NDB4V2

FG896	
Pin Number	A3PE3000 Function
AJ21	IO173PDB4V2
AJ22	IO163NDB4V1
AJ23	IO163PDB4V1
AJ24	IO167NPB4V1
AJ25	VCC
AJ26	IO156NPB4V0
AJ27	VCC
AJ28	TMS
AJ29	GND
AJ30	GND
AK2	GND
AK3	GND
AK4	IO217PPB5V2
AK5	GND
AK6	IO215PPB5V2
AK7	GND
AK8	IO207NDB5V1
AK9	IO207PDB5V1
AK10	IO201NDB5V0
AK11	IO201PDB5V0
AK12	IO193NDB4V4
AK13	IO193PDB4V4
AK14	IO197PDB5V0
AK15	IO191NDB4V4
AK16	IO191PDB4V4
AK17	IO189NDB4V4
AK18	IO189PDB4V4
AK19	IO179PPB4V3
AK20	IO175NDB4V2
AK21	IO175PDB4V2
AK22	IO169NDB4V1
AK23	IO169PDB4V1
AK24	GND
AK25	IO167PPB4V1
AK26	GND
AK27	GDC2/IO156PPB4V0

Revision	Changes	Page
v2.1 (continued)	The words "ambient temperature" were added to the temperature range in the "Temperature Grade Offerings", "Speed Grade and Temperature Grade Matrix", and "Speed Grade and Temperature Grade Matrix" sections.	1-I
	The "Clock Conditioning Circuit (CCC) and PLL" section was updated.	1-I
	The caption "Main (chip)" in Figure 2-9 • Overview of Automotive ProASIC3 VersaNet Global Network was changed to "Chip (main)."	2-9
	The T_J parameter in Table 3-2 • Recommended Operating Conditions was changed to T_A, ambient temperature, and table notes 4–6 were added.	3-2
	The "PLL Macro" section was updated to add information on the VCO and PLL outputs during power-up.	2-15
v2.0 (April 2007)	In the "Temperature Grade Offerings" section, Ambient was deleted.	iii
	Ambient was deleted from "Temperature Grade Offerings".	iii
	Ambient was deleted from the "Speed Grade and Temperature Grade Matrix".	iv
	The "PLL Macro" section was updated to include power-up information.	2-15
	Table 2-13 • ProASIC3E CCC/PLL Specification was updated.	2-30
	Figure 2-19 • Peak-to-Peak Jitter Definition is new.	2-18
	The "SRAM and FIFO" section was updated with operation and timing requirement information.	2-21
	The "RESET" section was updated with read and write information.	2-25
	The "RESET" section was updated with read and write information.	2-25
	The "Introduction" in the "Advanced I/Os" section was updated to include information on input and output buffers being disabled.	2-28
	In the Table 2-15 • Levels of Hot-Swap Support, the ProASIC3 compliance descriptions were updated for levels 3 and 4.	2-34
	Table 2-45 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3E Devices was updated.	2-64
	Notes 3, 4, and 5 were added to Table 2-17 • Comparison Table for 5 V–Compliant Receiver Scheme. 5 x 52.72 was changed to 52.7 and the Maximum current was updated from 4 x 52.7 to 5 x 52.7.	2-40
	The "VCCPLF PLL Supply Voltage" section was updated.	2-50
	The "VPUMP Programming Supply Voltage" section was updated.	2-50
	The "GL Globals" section was updated to include information about direct input into quadrant clocks.	2-51
	VJTAG was deleted from the "TCK Test Clock" section.	2-51
	In Table 2-22 • Recommended Tie-Off Values for the TCK and TRST Pins, TSK was changed to TCK in note 2. Note 3 was also updated.	2-51
	Ambient was deleted from Table 3-2 • Recommended Operating Conditions. VPUMP programming mode was changed from "3.0 to 3.6" to "3.15 to 3.45".	3-2
	Note 3 is new in Table 3-4 • Overshoot and Undershoot Limits (as measured on quiet I/Os).	3-2
	In EQ 3-2, 150 was changed to 110 and the result changed to 5.88.	3-5

Microsemi Corporate Headquarters
One Enterprise, Aliso Viejo,
CA 92656 USA

Within the USA: +1 (800) 713-4113
Outside the USA: +1 (949) 380-6100
Sales: +1 (949) 380-6136
Fax: +1 (949) 215-4996

E-mail: sales.support@microsemi.com

Microsemi Corporation (MSCC) offers a comprehensive portfolio of semiconductor and system solutions for communications, defense & security, aerospace and industrial markets. Products include high-performance and radiation-hardened analog mixed-signal integrated circuits, FPGAs, SoCs and ASICs; power management products; timing and synchronization devices and precise time solutions, setting the world's standard for time; voice processing devices; RF solutions; discrete components; security technologies and scalable anti-tamper products; Ethernet solutions; Power-over-Ethernet ICs and midspans; as well as custom design capabilities and services. Microsemi is headquartered in Aliso Viejo, Calif., and has approximately 3,600 employees globally. Learn more at **www.microsemi.com**.

51700098-15/06.15